VERSION WITH MARKINGS TO SHOW CHANGES MADE

The paragraph beginning on page 14, line 1 has been amended as follows:

-- The active element and the package, prepared as described above, are positioned so that the source electrode 4 of the active element faces/abuts to the Au plating 11 on the heat sink 9 of the package, and the active element and the package are bonded to each other by thermal pressure bonding for mounting, leaving a void 14 between the Au plating 11 and the Aluminum nitride 5, as show in Fig. 9.--

The paragraph beginning on page 15, line 15 has been amended as follows:

--The active element and the package, prepared as described above, are positioned so that the source electrode 4 of the active element faces the Au plating 11 on the heat sink 9 of the package, and so that the drain electrode 3 faces the aluminum nitride 5, leaving a void (14) between the Au plating and the aluminum nitride 5. In this state, the active element and the package are bonded to each other by thermal pressure bonding for mounting, as shown in Fig. 9. –

Claims 1, 2, 4, 5, and 7- 9, 11-20 have been canceled.

Claim 3 has been amended as follows:

3. (Amended) A semiconductor device wherein a first terminal of [the] an active element is connected via an electrically conductive member to a heat sink member, and wherein a second terminal of the active element transmits heat to said heat sink member via at

least an insulating member interposed in between, wherein a void is formed between said conductive member and said insulating member.

Claim 10 has been amended as follows:

10. (Amended) A semiconductor device as defined in claim [9] 21 wherein said insulating member is arranged on at least one of (a) a terminal surface of said active element and/or (b) a heat sink member side of the package used for mounting the active element.